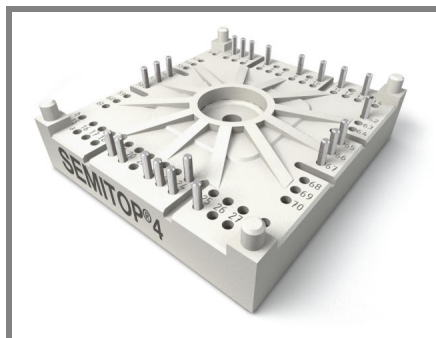




SEMITOP® 4

IGBT Module

SK50GD126T

Preliminary Data

Features

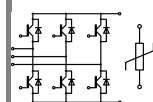
- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

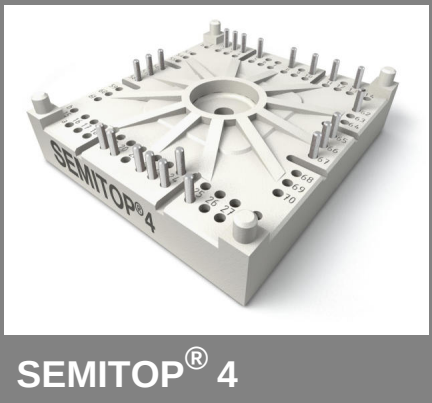
- Inverter up to 28 kVA
- Typ. motor power 15 kW

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}	$T_j = 25\text{ °C}$	1200	V
I_C	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$	68 A
		$T_s = 70\text{ °C}$	52 A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	100	A
V_{GES}		± 20	V
t_{psc}	$V_{CC} = 600\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 125\text{ °C}$ $V_{CES} < 1200\text{ V}$	10	μs
Inverse Diode			
I_F	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$	62 A
		$T_s = 70\text{ °C}$	46 A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	100	A
Module			
$I_{t(RMS)}$			A
T_{vj}		-40 ... +150	$^{\circ}\text{C}$
T_{stg}		-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 2\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$		0,0067	
		$T_j = 125\text{ °C}$			
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$	$T_j = 25\text{ °C}$		600	
		$T_j = 125\text{ °C}$			
V_{CE0}		$T_j = 25\text{ °C}$		1	
		$T_j = 125\text{ °C}$		0,9	
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$		14	
		$T_j = 125\text{ °C}$		22	
$V_{CE(sat)}$	$I_{Cnom} = 50\text{ A}$, $V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$		1,7	
		$T_j = 125\text{ °C}_{chiplev.}$		2	
C_{ies}	$V_{CE} = 25$, $V_{GE} = 0\text{ V}$			3,6	
C_{oes}		$f = 1\text{ MHz}$		0,188	
C_{res}				0,163	
$t_{d(on)}$	$R_{Gon} = 8\text{ }\Omega$	$V_{CC} = 600\text{ V}$		115	
t_r		$I_C = 50\text{ A}$		28	
E_{on}	$R_{Goff} = 8\text{ }\Omega$	$T_j = 125\text{ °C}$		4,6	
$t_{d(off)}$		$V_{GE} = -7 / +15\text{ V}$		509	
t_f				100	
E_{off}				6,3	
$R_{th(j-s)}$	per IGBT			0,6	



GD-T



IGBT Module

SK50GD126T

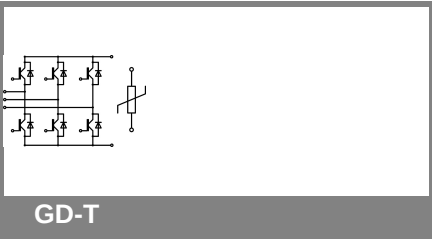
Preliminary Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

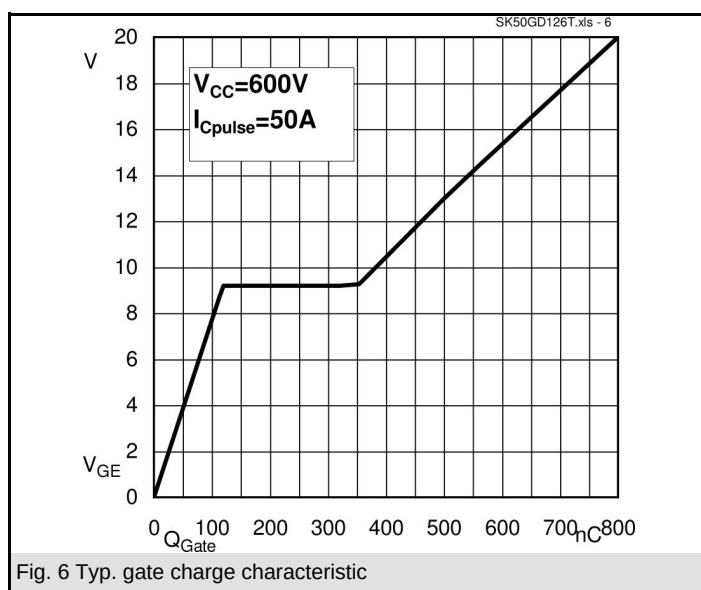
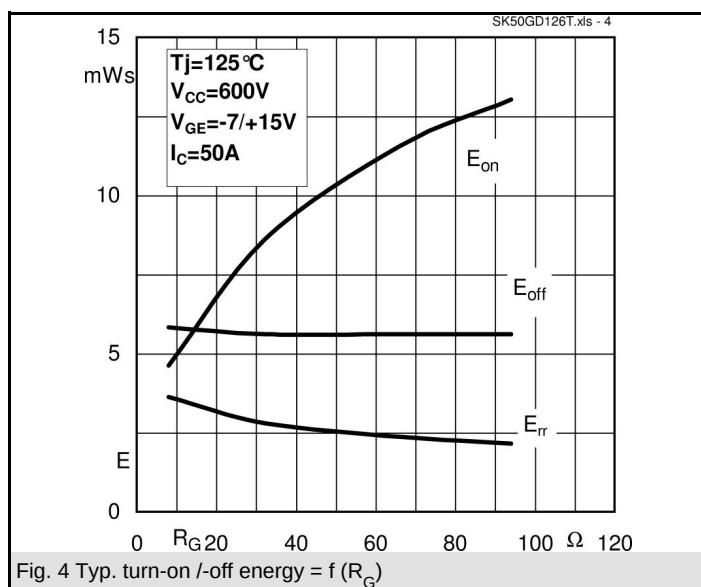
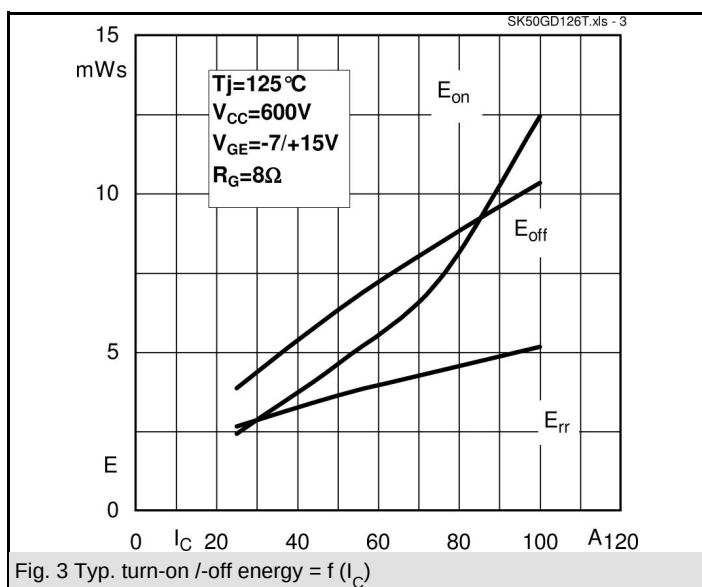
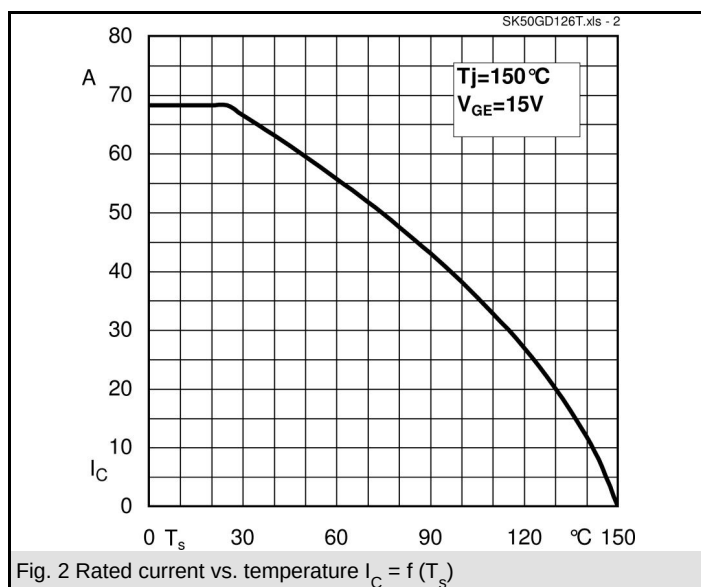
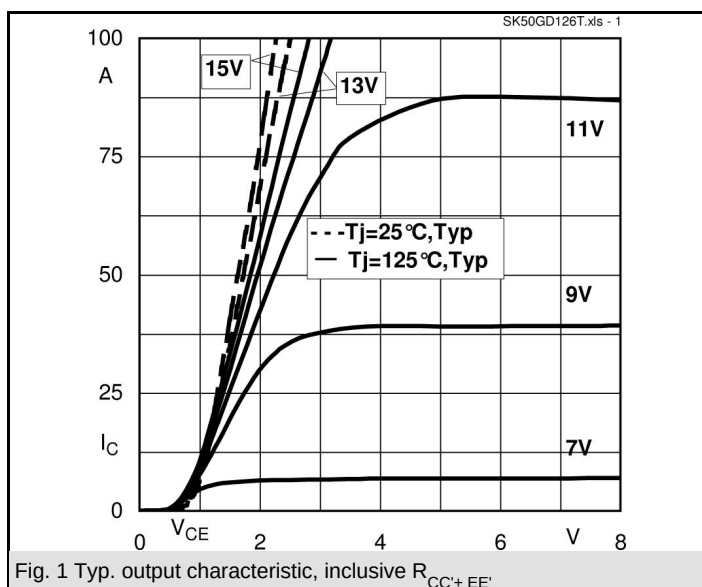
- Inverter up to 28 kVA
- Typ. motor power 15 kW

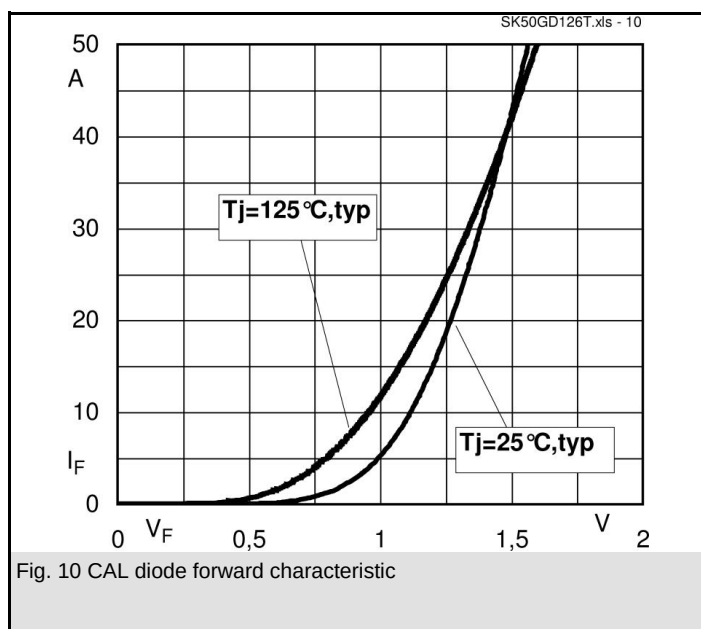
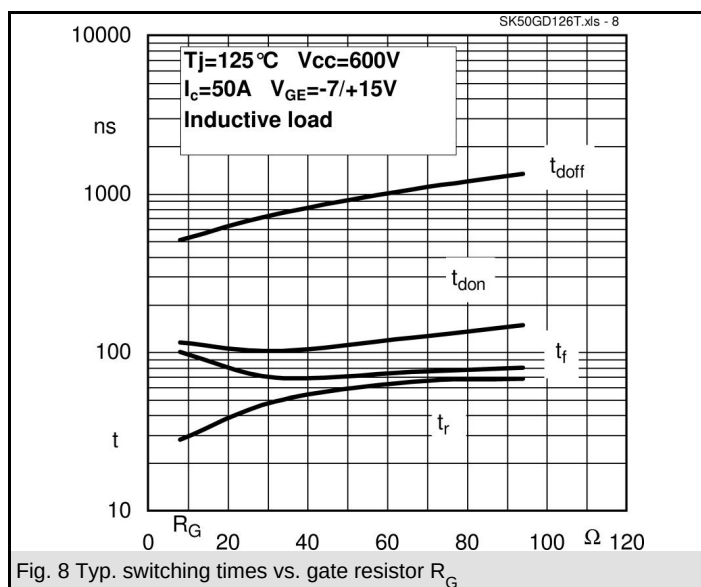
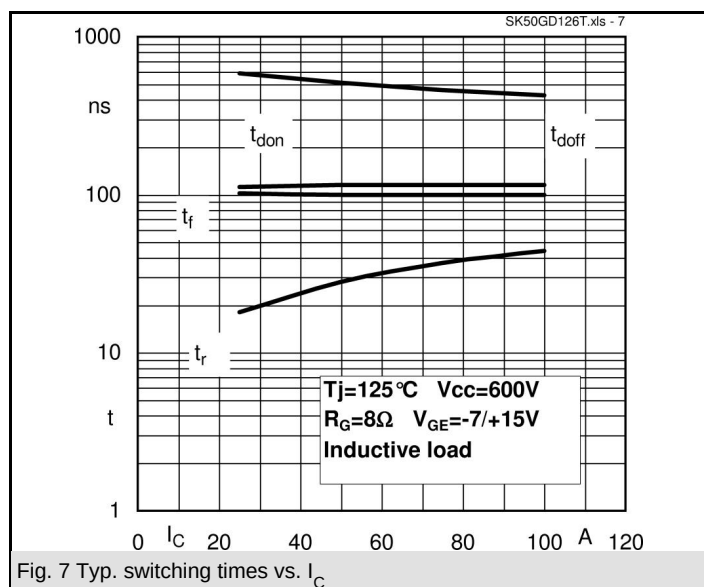


Characteristics						
Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
V _F = V _{EC}	I _{Fnom} = 50 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,35		V
		T _j = 125 °C _{chiplev.}		1,35		V
V _{F0}		T _j = 25 °C		0,95		V
		T _j = 125 °C		0,85		V
r _F		T _j = 25 °C		8		mΩ
		T _j = 125 °C		10		mΩ
I _{RRM}	I _F = 50 A	T _j = 125 °C		30		A
Q _{rr}	di/dt = 500 A/μs			10		μC
E _{rr}	V _{CC} = 600V			3,6		mJ
R _{th(j-s)D}	per diode			1		K/W
M _s	to heat sink		2,5		2,75	Nm
w				60		g
Temperature sensor						
R ₁₀₀	T _s =100°C (R ₂₅ =5kΩ)			493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

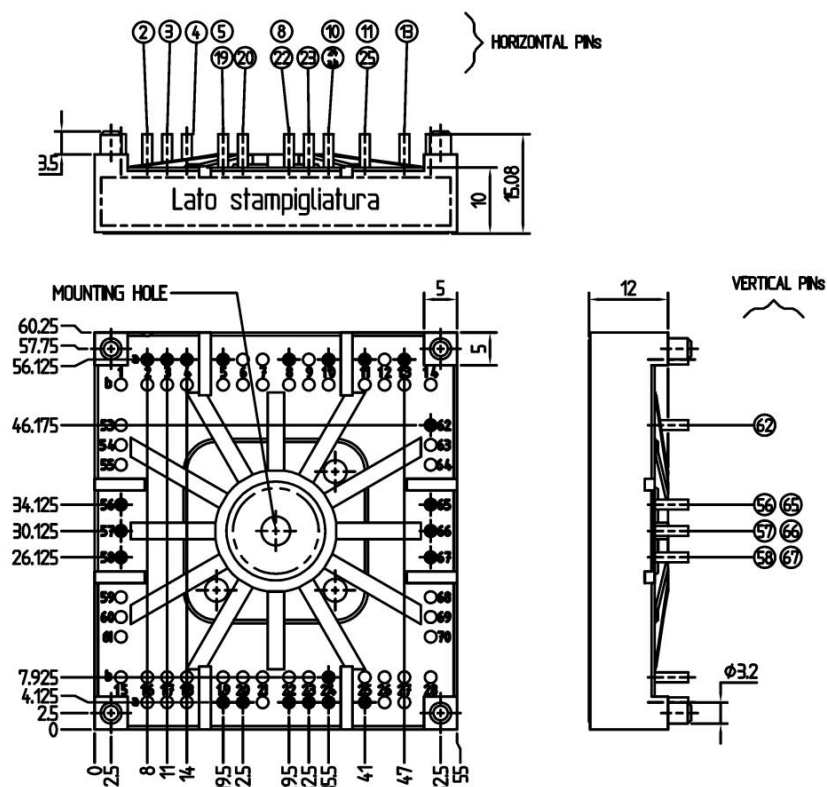
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



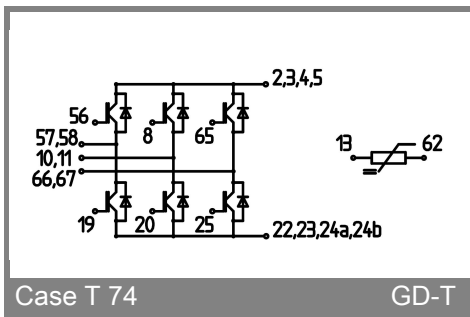


UL recognized file

no. E 63 532



Case T74 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



Case T 74

GD-T